SLLS587C – NOVEMBER 2003 – REVISED JANUARY 2008

QUAD DIFFERENTIAL PECL RECEIVERS

Check for Samples: TB3R1, TB3R2

FEATURES

- **Low-Voltage Functional Replacements for the Agere BRF1A, BRF2A, BRS2A, and BRS2B**
- **Pin-Equivalent to General Trade 26LS32 Devices**
- **High-Input Impedance Approximately 8 kΩ**
- **3.5-ns Maximum Propagation Delay**
- **TB3R1 Provides 50-mV Hysteresis**
- **TB3R2 With -125-mV Threshold Offset for Preferred State Output**
- **-0.5-V to 5.2-V Common Mode Range**
- **Single 3.3 V ±10% Supply**
- **Slew Rate Limited (0.5 ns min 80% to 20%)**
- **TB3R2 Output Defaults to Logic 1 When Inputs Left Open or Shorted to V_{CC} or GND**
- **ESD Protection HBM > 3 kV, CDM > 2 kV**
- **Operating Temperature Range: -40°C to 85°C**
- **Available SOIC (D) Package**

APPLICATIONS

- **Digital Data or Clock Transmission Over Balanced Lines**

DESCRIPTION

These quad differential receivers accept digital data over balanced transmission lines. They translate differential input logic levels to TTL output logic levels.

The TB3R1 is a pin- and function-compatible replacement for the Agere Systems BRF1A and BRF2A; it includes 3-kV HBM and 2-kV CDM ESD protection.

The TB3R2 is a pin- and function-compatible replacement for the Agere Systems BRS2A and BRS2B and incorporates a -125-mV receiver input offset, preferred state output, 3-kV HBM and 2-kV CDM ESD protection. The TB3R2 preferred state feature places the output in the high state when the inputs are open, shorted to ground, or shorted to the power supply.

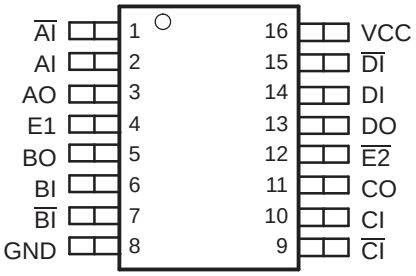
The power-down loading characteristics of the receiver input circuit are approximately 8 kΩ relative to the power supplies; hence they do not load the transmission line when the circuit is powered down.

The package for these differential line receivers is the 16-pin SOIC (D) package.

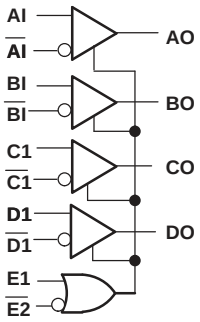
The enable inputs of this device include internal pullup resistors of approximately 40 kΩ that are connected to V_{CC} to ensure a logical high level input if the inputs are open circuited.

PIN ASSIGNMENTS

D PACKAGE
(TOP VIEW)



FUNCTIONAL BLOCK DIAGRAM



Enable Truth Table

E1	$\overline{E2}$	CONDITION
0	0	Active
1	0	Active
0	1	Disabled
1	1	Active

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION

PART NUMBER	PART MARKING	Package	LEAD FIISH	STATUS
TB3R1D	TB3R1	SOIC	NiPdAu	Production
TB3R2D	TB3R2	SOIC	NiPdAu	Production

POWER DISSIPATION RATINGS

PACKAGE	CIRCUIT BOARD MODEL	POWER RATING $T_A \leq 25°C$	THERMAL RESISTANCE, JUNCTION-TO-AMBIENT WITH NO AIR FLOW	DERATING FACTOR(1) $T_A \geq 25°C$	POWER RATING $T_A = 85°C$
D	Low-K(1)	763 mW	131.1°C/W	7.6 mW/°C	305 mW
	High-K(2)	1190 mW	84.1°C/W	11.9 mW/°C	475 mW
DW	Low-K(1)	831 mW	120.3°C/W	8.3 mW/°C	332 mW
	High-K(2)	1240 mW	80.8°C/W	12.4 mW/°C	494 mW

(1) In accordance with the low-K thermal metric definitions of EIA/JESD51-3.
(2) In accordance with the high-K thermal metric definitions of EIA/JESD51-7.

THERMAL CHARACTERISTICs

PARAMETER		PACKAGE	VALUE	UNIT
θ_{JB}	Junction-to-Board Thermal Resistance	D	47.5	°C/W
		DW	53.7	°C/W
θ_{JC}	Junction-to-Case Thermal Resistance	D	44.2	°C/W
		DW	47.1	°C/W

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

			UNIT
Supply voltage, V_{CC}			0 V to 6 V
Magnitude of differential bus (input) voltage, $\lvert V_{AI} - V\rvert$, $\lvert V_{BI} - V\rvert$, $\lvert V_{CI} - V\rvert$, $\lvert V_{DI} - V\rvert$			6.5 V
ESD	Human Body Model(2)	All pins	±3 kV
	Charged-Device Model(3)	All pins	±2 kV
Continuous power dissipation			See Dissipation Rating Table
Storage temperature, T_{stg}			-65°C to 150°C

(1) Stresses beyond those listed under„ absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under„ recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
(3) Tested in accordance with JEDEC Standard 22, Test Method C101.

RECOMMENDED OPERATING CONDITIONS

	MIN	Nom	MAX	UNIT
Supply voltage, V_{CC}	3	3.3	3.6	V
Bus pin input voltage, V_{AI}, V, V_{BI}, V, V_{CI}, V, V_{DI}, V	-0.6 (1)		5.3	V
Magnitude of differential input voltage, $\|V_{AI} - V\|$, $\|V_{BI} - V\|$, $\|V_{CI} - V\|$, $\|V_{DI} - V\|$	0.1		5	V
Operating free-air temperature, T_A	-40		85	°C

(1) The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet, unless otherwise noted.

DEVICE ELECTRICAL CHARACTERISTICS

over operating free-air temperature range unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{CC}	Supply current (1)	Outputs disabled			34	mA
		Outputs enabled			32	mA

(1) Current is dc power draw as measured through GND pin and does not include power delivered to load.

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range unless otherwise noted

parameter		test conditions		min	typ	max	unit
V_{OL}	Output low voltage	V_{CC} = 3 V,	I_{OL} = 8 mA			0.4	V
V_{OH}	Output high voltage	V_{CC} = 3 V,	I_{OH} = -400 µA	2.4			V
V_{IL}	Low level enable input voltage (1)	V_{CC} = 3.6 V				0.8	V
V_{IH}	High level enable input voltage (1)	V_{CC} = 3.6 V		2			V
V_{IK}	Enable input clamp voltage	V_{CC} = 3 V,	I_I = -5 mA			-1 (2)	V
V_{TH+}	Positive-going differential input threshold voltage (1), (V_{xI} - V)	x = A, B, C, or D	TB3R1			100	mV
			TB3R2 (3)			-50	mV
V_{TH-}	Negative-going differential input threshold voltage (1), (V_{xI} - V)	x = A, B, C, or D	TB3R1			-100 (2)	mV
			TB3R2 (3)			-200 (2)	mV
V_{HYST}	Differential input threshold voltage hysteresis, (V_{TH+} - $V_{TH\_}$)	TB3R1			50		mV
I_{OZL}	Output off-state current, (High-Z)	V_{CC} = 3.6 V	V_O = 0.4 V			-20 (2)	µA
I_{OZH}			V_O = 2.4 V			20	µA
I_{OS}	Output short circuit current (4)	V_{CC} = 3.6 V				-100 (2)	mA
I_{IL}	Enable input low current	V_{CC} = 3.6 V,	V_{IN} = 0.4 V			-400 (2)	µA
I_{IH}	Enable input high current	V_{CC} = 3.6 V	V_{IN} = 2.7 V			20	µA
	Enable input reverse current		V_{IN} = 3.6 V			100	µA
II_L	Differential input low current	V_{CC} = 3.6 V,	V_{IN} = -1.2 V			-2 (2)	mA
I_{IH}	Differential input high current	V_{CC}= 3.6 V,	V_{IN} = 5.3 V			1	mA
R_O	Output resistance				20		Ω

(1) The input levels and difference voltage provide no noise immunity and should be tested only in a static, noise-free environment.
(2) This parameter is listed using a magnitude and polarity/direction convention, rather than an algebraic convention, to match the original Agere data sheet.
(3) Outputs of unused receivers assume a logic 1 level when the inputs are left open. (It is recomended that all unused positive inputs be tied to the positive power supply. No external series resistor is required.)
(4) Test must be performed one lead at a time to prevent damage to the device.

SWITCHING CHARACTERISTICS

over operating free-air temperature range unless otherwise noted

parameter		test conditions	min	typ	max	unit
t_{PLH}	Propagation delay time, low-to-high-level output	C_L = 0 pF(1), See Figure 2 and Figure 4		1.8	3.5	ns
t_{PHL}	Propagation delay time, high-to-low-level output			1.8	3.5	
t_{PLH}	Propagation delay time, low-to-high-level output	C_L = 15 pF, See Figure 2 and Figure 4		2.3	4	ns
t_{PHL}	Propagation delay time, high-to-low-level output			2.3	4	
t_{PHZ}	Output disable time, high-level-to-high-impedance output(2)	C_L = 5 pF See Figure 3 and Figure 5		4.4	12	ns
t_{PLZ}	Output disable time, low-level-to-high-impedance output(2)			3.3	12	ns
t_{skew1}	Pulse width distortion, $\|t_{PHL} - t_{PLH}\|$	C_L = 10 pF, See Figure 2 and Figure 4			0.7	ns
		C_L = 150 pF, See Figure 2 and Figure 4			4	ns
$\Delta t_{skew1p-p}$	Part-to-part output waveform skew(3)	C_L = 10 pF, T_A = 75°C, See Figure 2 and Figure 4		0.8	1.4	ns
		C_L = 10 pF, T_A = -40°C to 85°C, See Figure 2 and Figure 4			1.5	ns
Δt_{skew}	Same part output waveform skew(3)	C_L = 10 pF, See Figure 2 and Figure 4			0.3	ns
t_{PZH}	Output enable time, high-impedance-to-high-level output(2)	C_L = 10 pF, See Figure 3 and Figure 4		6	12	ns
t_{PZL}	Output enable time, high-impedance-to-low-level output(2)			4	12	ns
t_{TLH}	Rise time (20%-80%)	C_L = 10 pF, See Figure 2 and Figure 4	0.5		2	ns
t_{THL}	Fall time (80%-20%)		0.5		2	ns

(1) The propagation delay values with a 0 pF load are based on design and simulation.
(2) See Table 1.
(3) Output waveform skews are when devices operate with the same supply voltage, same temperature, have the same packages and the same test circuits.

TYPICAL CHARACTERISTICS

Parametric values specified under the Electrical Characteristics and Timing Characteristics sections for the data transmission driver devices are measured with the following output load circuits.

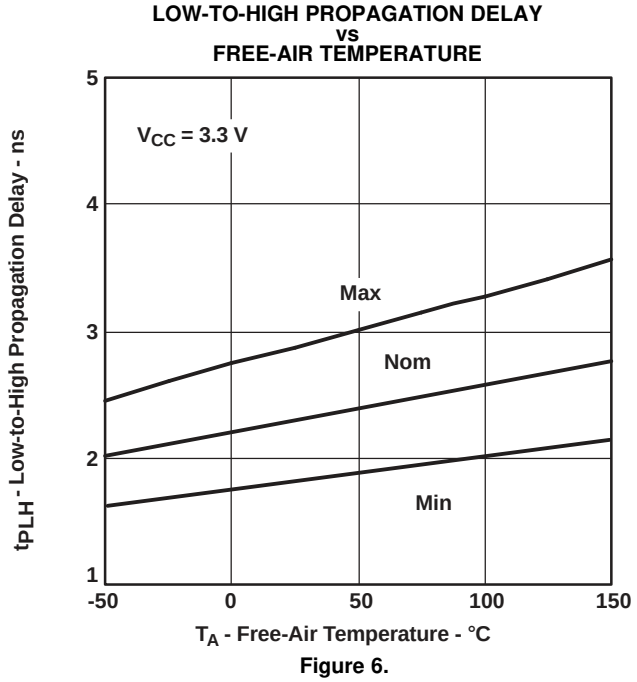


Figure 6.

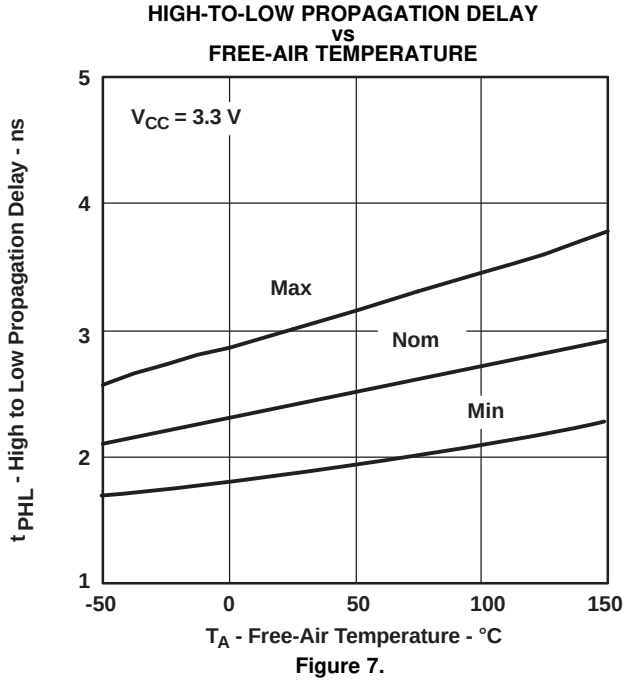


Figure 7.

TYPICAL CHARACTERISTICS (continued)

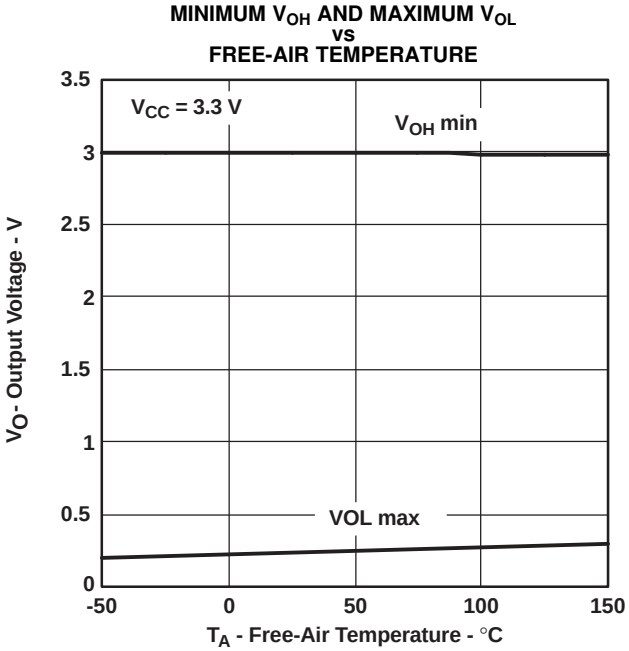


Figure 8.

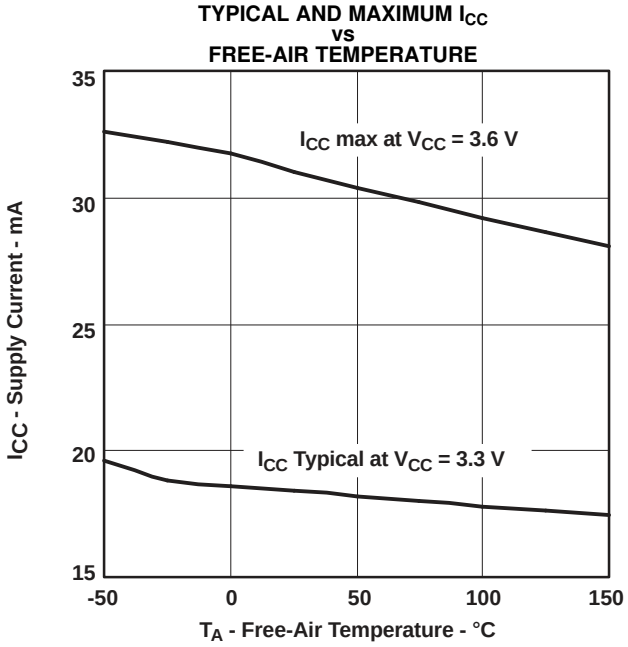


Figure 9.

APPLICATION INFORMATION

Power Dissipation

The power dissipation rating, often listed as the package dissipation rating, is a function of the ambient temperature, T_A, and the airflow around the device. This rating correlates with the device's maximum junction temperature, sometimes listed in the absolute maximum ratings tables. The maximum junction temperature accounts for the processes and materials used to fabricate and package the device, in addition to the desired life expectancy.

There are two common approaches to estimating the internal die junction temperature, T_J. In both of these methods, the device internal power dissipation P_D needs to be calculated This is done by totaling the supply power(s) to arrive at the system power dissipation:

$$\sum(V_{Sn} \times I_{Sn}) \quad (1)$$

and then subtracting the total power dissipation of the external load(s):

$$\sum(V_{Ln} \times I_{Ln}) \quad (2)$$

The first T_J calculation uses the power dissipation and ambient temperature, along with one parameter: θ_{JA}, the junction-to-ambient thermal resistance, in degrees Celsius per watt.

The product of P_D and θ_{JA} is the junction temperature rise above the ambient temperature. Therefore:

$$T_J = T_A + (P_D \times \theta_{JA}) \quad (3)$$

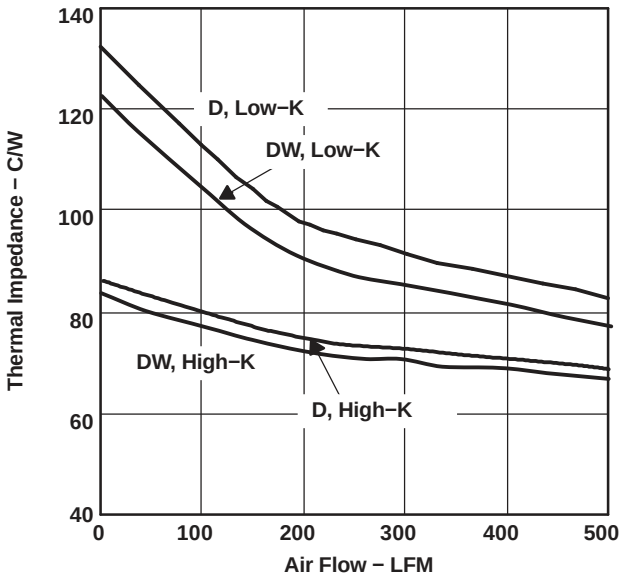


Figure 10. Thermal Impedance vs Air Flow

Note that θ_{JA} is highly dependent on the PCB on which the device is mounted, and on the airflow over the device and PCB. JEDEC/EIA has defined standardized test conditions for measuring θ_{JA}. Two commonly used conditions are the low-K and the high-K boards, covered by EIA/JESD51-3 and EIA/JESD51-7 respectively. Figure 10 shows the low-K and high-K values of θ_{JA} versus air flow for this device and its package options.

The standardized θ_{JA} values may not accurately represent the conditions under which the device is used. This can be due to adjacent devices acting as heat sources or heat sinks, to nonuniform airflow, or to the system PCB having significantly different thermal characteristics than the standardized test PCBs. The second method of system thermal analysis is more accurate. This calculation uses the power dissipation and ambient temperature, along with two device and two system-level parameters:

- θ_{JC}, the junction-to-case thermal resistance, in degrees Celsius per watt
- θ_{JB}, the junction-to-board thermal resistance, in degrees Celsius per watt
- θ_{CA}, the case-to-ambient thermal resistance, in degrees Celsius per watt
- θ_{BA}, the board-to-ambient thermal resistance, in degrees Celsius per watt.

In this analysis, there are two parallel paths, one through the case (package) to the ambient, and another through the device to the PCB to the ambient. The system-level junction-to-ambient thermal impedance, $\theta_{JA(S)}$, is the equivalent parallel impedance of the two parallel paths:

$$T_J = T_A + \left(P_D \times \theta_{JA(S)}\right) \quad (4)$$

where

$$\theta_{JA(S)} = \frac{\left[\left(\theta_{JC} + \theta_{CA}\right) \times \left(\theta_{JB} + \theta_{BA}\right)\right]}{\left(\theta_{JC} + \theta_{CA} + \theta_{JB} + \theta_{BA}\right)} \quad (5)$$

The device parameters θ_{JC} and θ_{JB} account for the internal structure of the device. The system-level parameters θ_{CA} and θ_{BA} take into account details of the PCB construction, adjacent electrical and mechanical components, and the environmental conditions including airflow. Finite element (FE), finite difference (FD), or computational fluid dynamics (CFD) programs can determine θ_{CA} and θ_{BA}. Details on using these programs are beyond the scope of this data sheet, but are available from the software manufacturers.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TB3R1D	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-2-250C-1YEAR/ Level-1-220C-UNLIM	-40 to 85	TB3R1	Samples
TB3R1DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-2-250C-1YEAR/ Level-1-220C-UNLIM	-40 to 85	TB3R1	Samples
TB3R2D	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-2-250C-1YEAR/ Level-1-220C-UNLIM	-40 to 85	TB3R2	Samples
TB3R2DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-2-250C-1YEAR/ Level-1-220C-UNLIM	-40 to 85	TB3R2	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
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Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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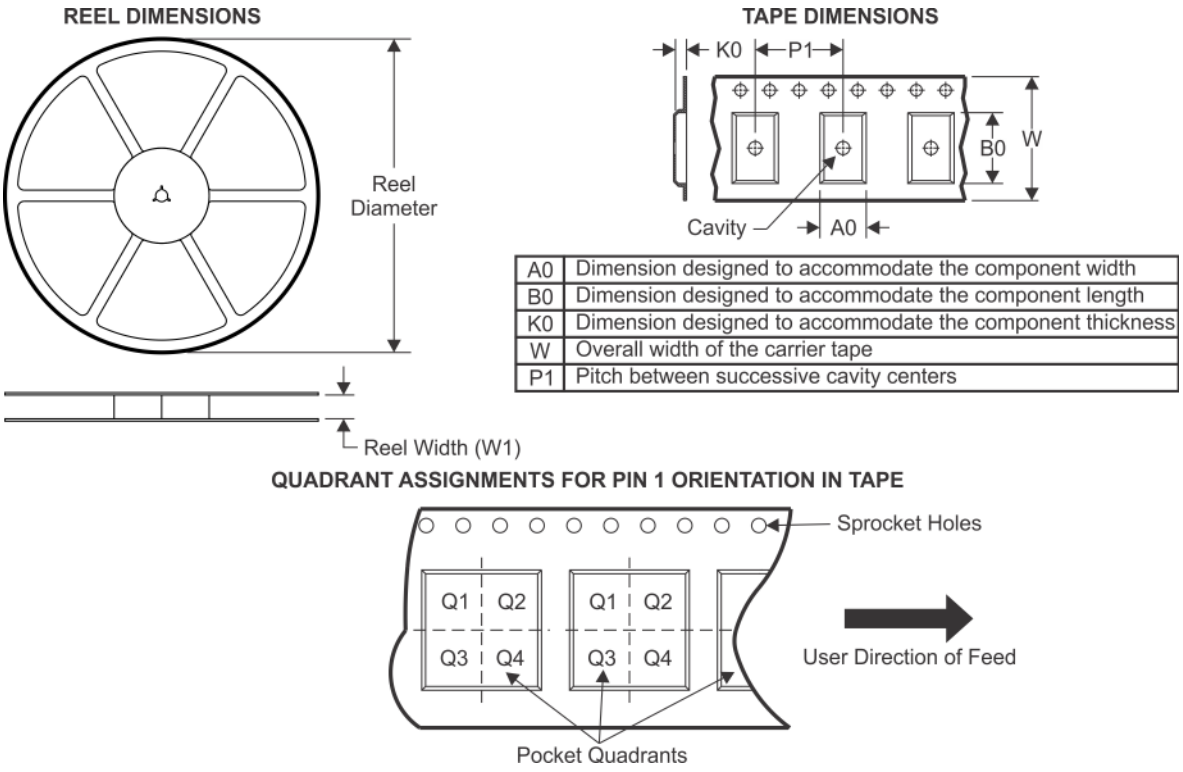
TAPE AND REEL INFORMATION

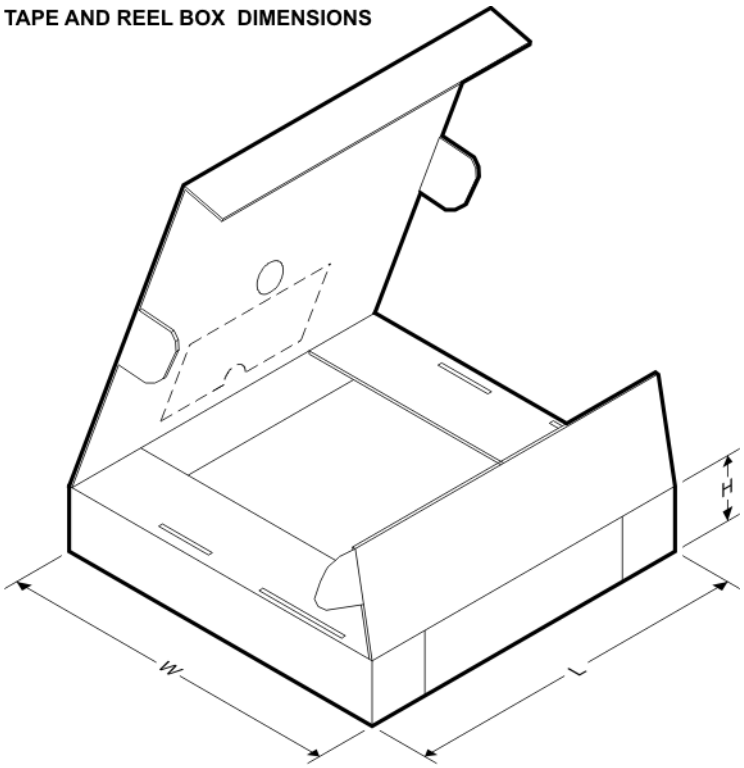


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TB3R1DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TB3R2DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

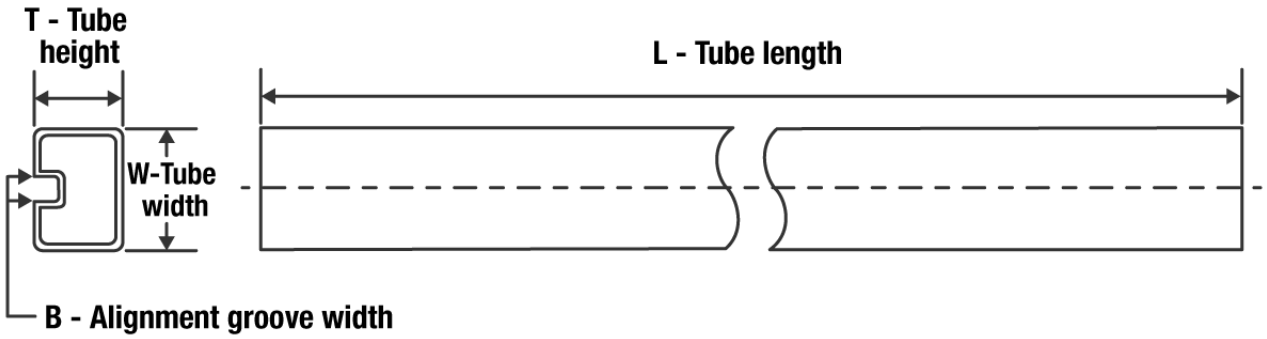
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TB3R1DR	SOIC	D	16	2500	350.0	350.0	43.0
TB3R2DR	SOIC	D	16	2500	350.0	350.0	43.0

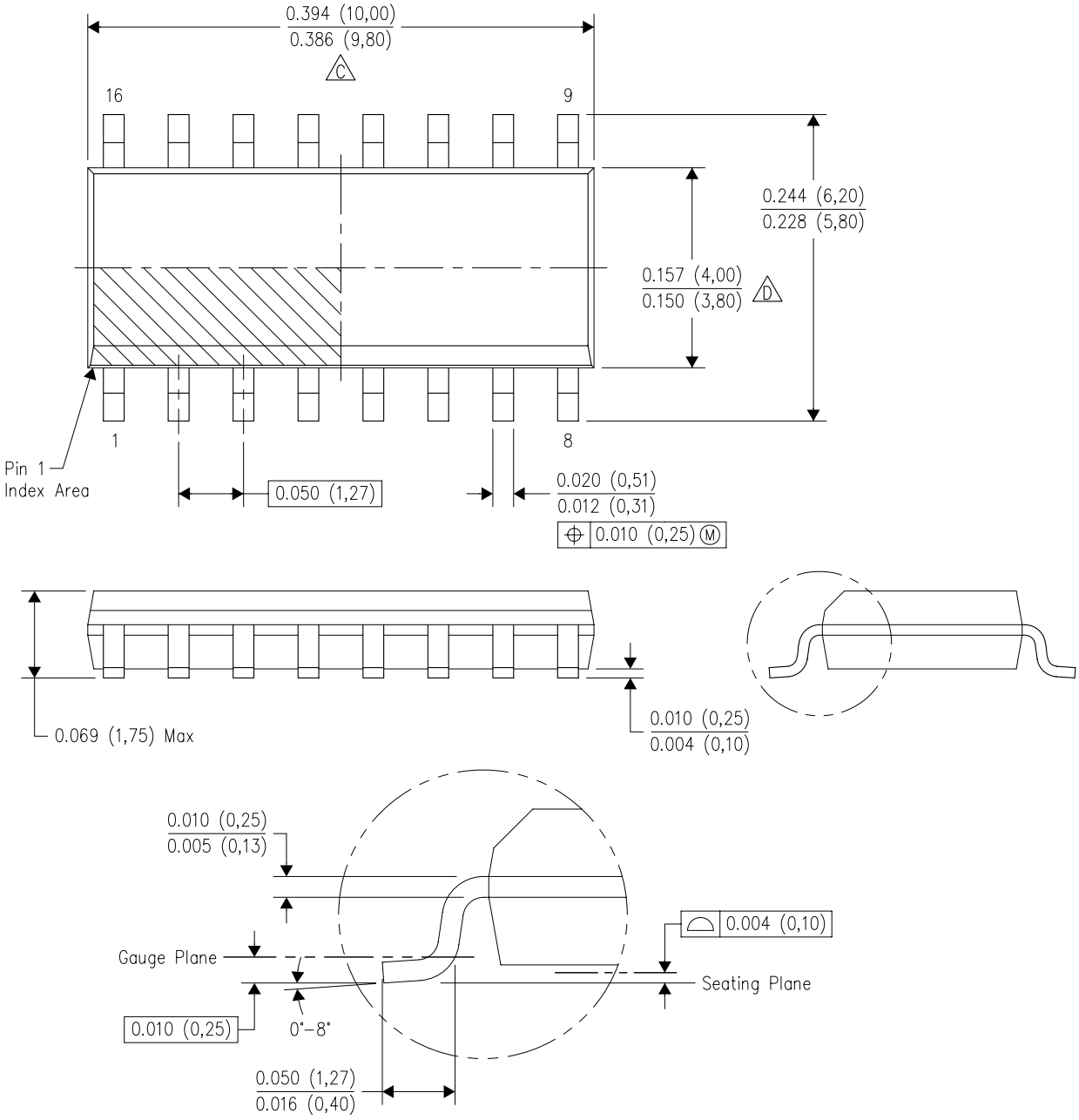
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TB3R1D	D	SOIC	16	40	505.46	6.76	3810	4
TB3R2D	D	SOIC	16	40	505.46	6.76	3810	4

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

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